Marc Meuris

List of Publications by Year
in descending order

203 papers	5,706 citations	81839 39 h-index	106281 65 g-index
203 all docs	203 docs citations	203 times ranked	3870 citing authors

#	Article	IF	Citations
1	A Novel Strategy for the Application of an Oxide Layer to the Front Interface of Cu(In,Ga)Se₂ Thin Film Solar Cells: Al₂O₃/HfO₂ Multi-Stack Design With Contact Openings. IEEE Journal of Photovoltaics, 2022, 12, 301-308.	1.5	4
2	Comparison of a bottom-up and a top-down approach for the creation of contact openings in a multi-stack oxide layer at the front interface of Cu(In,Ga)Se2. Solar Energy, 2022, 237, 161-172.	2.9	1
3	Round-robin of damp heat tests using CIGS solar cells. Solar Energy, 2021, 214, 393-399.	2.9	2
4	Novel cost-effective approach to produce nano-sized contact openings in an aluminum oxide passivation layer up to 30 nm thick for CIGS solar cells. Journal Physics D: Applied Physics, 2021, 54, 234004.	1.3	4
5	Bias dependent admittance spectroscopy: the impact of sodium supply on the Cu(In,Ga)Se2 growth.. , 2021, , .		0
6	Comparative Study of Al₂O₃ and HfO₂ for Surface Passivation of Cu(In,Ga)Se₂ Thin Films: An Innovative Al₂O₃/HfO₂ Multistack Design. Physica Status Solidi (A) Applications and Materials Science, 2021, 218, 2100073.	0.8	5
7	A multi-stack Al₂O₃/HfO₂ design with contact openings for front surface of Cu(In,Ga)Se₂ solar cells. , 2021, , .		1
8	Detrimental Impact of Na Upon Rb Postdeposition Treatments of Cu(In,Ga)Se 2 Absorber Layers. Solar Rrl, 2021, 5, 2100390.	3.1	4
9	Ultrathin Cu(In,Ga)Se2 Solar Cells with Ag/AlOx Passivating Back Reflector. Energies, 2021, 14, 4268.	1.6	4
10	Dominant Processing Factors in Two-Step Fabrication of Pure Sulfide CIGS Absorbers. Energies, 2021, 14, 4737.	1.6	4
11	Bias dependent admittance spectroscopy of thin film solar cells: KF post deposition treatment, accelerated lifetime testing, and their effect on the CVf loss maps. Solar Energy Materials and Solar Cells, 2021, 231, 111289.	3.0	1
12	Investigating the experimental space for two-step Cu(In,Ga)(S,Se)2 absorber layer fabrication: A design of experiment approach. Thin Solid Films, 2021, 738, 138958.	0.8	3
13	Innovative and industrially viable approach to fabricate AlOx rear passivated ultra-thin Cu(In, Ga)Se2 (CIGS) solar cells. Solar Energy, 2020, 207, 1002-1008.	2.9	23
14	Intermediate scale bandgap fluctuations in ultrathin Cu(In,Ga)Se2 absorber layers. Journal of Applied Physics, 2020, 128, 163102.	1.1	5
15	Study of Ammonium Sulfide Surface Treatment for Ultrathin Cu(In,Ga)Se₂ with Different Cu/(Gaâ€‰+â€‰In) Ratios. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000307.	0.8	5
16	Rear surface passivation of ultra-thin CIGS solar cells using atomic layer deposited HfO_x. EPJ Photovoltaics, 2020, 11, 10.	0.8	17
17	Inclusion of Water in Cu(In, Ga)Se2 Absorber Material During Accelerated Lifetime Testing. ACS Applied Energy Materials, 2020, 3, 5120-5125.	2.5	14
18	Impact of photovoltaic technology and feeder voltage level on the efficiency of faÃ§ade building-integrated photovoltaic systems. Applied Energy, 2020, 269, 115039.	5.1	9

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19	Sn Substitution by Ge: Strategies to Overcome the Open-Circuit Voltage Deficit of Kesterite Solar Cells. ACS Applied Energy Materials, 2020, 3, 5830-5839.	2.5	32
20	Bias-Dependent Admittance Spectroscopy of Thin-Film Solar Cells: Experiment and Simulation. IEEE Journal of Photovoltaics, 2020, 10, 1102-1111.	1.5	13
21	High <i>V</i>_{oc} upon KF Post-Deposition Treatment for Ultrathin Single-Stage Coevaporated Cu(In, Ga)Se₂ Solar Cells. ACS Applied Energy Materials, 2019, 2, 6102-6111.	2.5	22
22	Wide band gap kesterite absorbers for thin film solar cells: potential and challenges for their deployment in tandem devices. Sustainable Energy and Fuels, 2019, 3, 2246-2259.	2.5	19
23	Dielectric-Based Rear Surface Passivation Approaches for Cu(In,Ga)Se2 Solar Cellsâ€"A Review. Applied Sciences (Switzerland), 2019, 9, 677.	1.3	46
24	Crystallization properties of Cu2ZnGeSe4. Thin Solid Films, 2019, 670, 76-79.	0.8	10
25	Alkali treatment for single-stage co-evaporated thin CuIn0.7Ga0.3Se2 solar cells. Thin Solid Films, 2019, 671, 44-48.	0.8	13
26	A study to improve light confinement and rear-surface passivation in a thin-Cu(In, Ga)Se2 solar cell. Thin Solid Films, 2019, 669, 399-403.	0.8	18
27	Managing PV power injection and storage, enabling a larger direct consumption of renewable energy: A case study for the Belgian electricity system. Progress in Photovoltaics: Research and Applications, 2019, 27, 905-917.	4.4	3
28	Surface Passivation of CIGS Solar Cells Using Gallium Oxide. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700826.	0.8	36
29	Doping of Cu2ZnSnSe4 solar cells with Na+ or K+ alkali ions. Journal of Materials Chemistry A, 2018, 6, 2653-2663.	5.2	19
30	Wet Processing in State-of-the-Art Cu(In,Ga)(S,Se)₂ Thin Film Solar Cells. Solid State Phenomena, 2018, 282, 300-305.	0.3	3
31	Fabrication of high band gap kesterite solar cell absorber materials for tandem applications. Thin Solid Films, 2018, 660, 247-252.	0.8	13
32	Pâ€"N Junction Passivation in Kesterite Solar Cells by Use of Solution-Processed TiO2 Layer. IEEE Journal of Photovoltaics, 2017, 7, 1130-1135.	1.5	11
33	Synthesis and characterization of (Cd,Zn)S buffer layer for Cu2ZnSnSe4solar cells. Journal Physics D: Applied Physics, 2017, 50, 285501.	1.3	12
34	Modelling of Cu₂ZnSnSe₄-CdS-ZnO thin film solar cell. Materials Research Express, 2017, 4, 116403.	0.8	1
35	Interlaboratory comparison of photovoltaic performance measurements using CIGS solar cells. , 2017, , .		1
36	Effect of different alkali (Li, Na, K, Rb, Cs) metals on Cu 2 ZnSnSe 4 solar cells. Thin Solid Films, 2017, 633, 156-161.	0.8	52

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37	Effect of Sn/Zn/Cu precursor stack thickness on two-step processed kesterite solar cells. Thin Solid Films, 2017, 633, 127-130.	0.8	8
38	Effect of ammonium sulfide treatments on the surface properties of Cu2ZnSnSe4 thin films. Thin Solid Films, 2017, 633, 135-140.	0.8	7
39	Effect of the duration of a wet KCN etching step and post deposition annealing on the efficiency of Cu 2 ZnSnSe 4 solar cells. Thin Solid Films, 2017, 633, 166-171.	0.8	4
40	Effect of Cu content and temperature on the properties of Cu₂ZnSnSe₄solar cells. EPJ Photovoltaics, 2016, 7, 70304.	0.8	8
41	Progress in Cleaning and Wet Processing for Kesterite Thin Film Solar Cells. Solid State Phenomena, 2016, 255, 348-353.	0.3	2
42	Fabrication and characterization of ternary Cu8SiS6 and Cu8SiSe6 thin film layers for optoelectronic applications. Thin Solid Films, 2016, 616, 649-654.	0.8	6
43	KCN Chemical Etch for Interface Engineering in Cu₂ZnSnSe₄ Solar Cells. ACS Applied Materials & Interfaces, 2015, 7, 14690-14698.	4.0	62
44	Impact of the Cd²⁺ treatment on the electrical properties of Cu₂ZnSnSe₄ and Cu(In,Ga)Se₂ solar cells. Progress in Photovoltaics: Research and Applications, 2015, 23, 1608-1620.	4.4	28
45	Effect of selenium content of CuInSex alloy nanopowder precursors on recrystallization of printed CuInSe2 absorber layers during selenization heat treatment. Thin Solid Films, 2015, 582, 11-17.	0.8	9
46	Effect of the burn-out step on the microstructure of the solution-processed Cu(In,Ga)Se2 solar cells. Thin Solid Films, 2015, 583, 142-150.	0.8	4
47	Investigation of Properties Limiting Efficiency in Cu₂ZnSnSe₄-Based Solar Cells. IEEE Journal of Photovoltaics, 2015, 5, 649-655.	1.5	20
48	Physical and electrical characterization of high-performance Cu 2 ZnSnSe 4 based thin film solar cells. Thin Solid Films, 2015, 582, 224-228.	0.8	55
49	Surface Cleaning and Passivation Using (NH₄)₂S Treatment for Cu(In,Ga)Se₂ Solar Cells: A Safe Alternative to KCN. Advanced Energy Materials, 2015, 5, 1401689.	10.2	36
50	Selenization of printed Cuâ€“Inâ€“Se alloy nanopowder layers for fabrication of CuInSe2 thin film solar cells. Thin Solid Films, 2015, 582, 18-22.	0.8	11
51	Physical characterization of Cu2ZnGeSe4 thin films from annealing of Cuâ€“Znâ€“Ge precursor layers. Thin Solid Films, 2015, 582, 171-175.	0.8	31
52	Spectral currentâ€“voltage analysis of kesterite solar cells. Journal Physics D: Applied Physics, 2014, 47, 175101.	1.3	33
53	Microstructural analysis of 9.7% efficient Cu2ZnSnSe4 thin film solar cells. Applied Physics Letters, 2014, 105, .	1.5	19
54	Effect of Binder Content in Cuâ€“Inâ€“Se Precursor Ink on the Physical and Electrical Properties of Printed CuInSe₂ Solar Cells. Journal of Physical Chemistry C, 2014, 118, 27201-27209.	1.5	9

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55	Mechanical synthesis of high purity Cuâ€“Inâ€“Se alloy nanopowder as precursor for printed CISe thin film solar cells. Advanced Powder Technology, 2014, 25, 1254-1261.	2.0	10
56	18% Efficiency IBC Cell With Rear-Surface Processed on Quartz. IEEE Journal of Photovoltaics, 2013, 3, 684-689.	1.5	10
57	Characterization of defects in 9.7% efficient Cu2ZnSnSe4-CdS-ZnO solar cells. Applied Physics Letters, 2013, 103, .	1.5	199
58	Electrical characterization of Cu2ZnSnSe4 solar cells from selenization of sputtered metal layers. Thin Solid Films, 2013, 535, 348-352.	0.8	27
59	Impact of ammonium sulfide solution on electronic properties and ambient stability of germanium surfaces: towards Ge-based microelectronic devices. Journal of Materials Chemistry C, 2013, 1, 4105.	2.7	13
60	Liquid-Phase Adsorption of Sulfur on Germanium: Reaction Mechanism and Atomic Geometry. Journal of Physical Chemistry C, 2013, 117, 7451-7458.	1.5	6
61	Oxidation and Sulfidation of Germanium Surfaces: A Comparative Atomic Level Study of Different Passivation Schemes. ECS Transactions, 2013, 50, 569-579.	0.3	2
62	Integration of InGaAs Channel n-MOS Devices on 200mm Si Wafers Using the Aspect-Ratio-Trapping Technique. ECS Transactions, 2012, 45, 115-128.	0.3	39
63	InGaAs MOS Transistors Fabricated through a Digital-Etch Gate-Recess Process and the Influence of Forming Gas Anneal on Their Electrical Behavior. ECS Journal of Solid State Science and Technology, 2012, 1, P310-P314.	0.9	10
64	Oxide Trapping in the InGaAsâ€“$hbox{Al}_{2} hbox{O}_{3}$ System and the Role of Sulfur in Reducing the $ hbox{Al}_{2}hbox{O}_{3}$ Trap Density. IEEE Electron Device Letters, 2012, 33, 1544-1546.	2.2	23
65	Simulation Study of Performance for a 20-nm Gate Length In$_{f 0.53}$Ga$_{f 0.47}$As Implant Free Quantum Well MOSFET. IEEE Nanotechnology Magazine, 2012, 11, 808-817.	1.1	7
66	Adsorption of O₂ on Ge(100): Atomic Geometry and Site-Specific Electronic Structure. Journal of Physical Chemistry C, 2012, 116, 9925-9929.	1.5	13
67	Crystalline thinâ€foil silicon solar cells: where crystalline quality meets thinâ€film processing. Progress in Photovoltaics: Research and Applications, 2012, 20, 770-784.	4.4	74
68	The implant-free quantum well field-effect transistor: Harnessing the power of heterostructures. Thin Solid Films, 2012, 520, 3326-3331.	0.8	8
69	A Fast and Accurate Method to Study the Impact of Interface Traps on Germanium MOS Performance. IEEE Transactions on Electron Devices, 2011, 58, 938-944.	1.6	12
70	Low-Frequency Noise Characterization of Strained Germanium pMOSFETs. IEEE Transactions on Electron Devices, 2011, 58, 3132-3139.	1.6	19
71	A Combined Interface and Border Trap Model for High-Mobility Substrate Metalâ€“Oxideâ€“Semiconductor Devices Applied to $hbox{In}_{0.53} hbox{Ga}_{0.47}hbox{As}$ and InP Capacitors. IEEE Transactions on Electron Devices, 2011, 58, 3890-3897.	1.6	96
72	Experimental and theoretical investigation of defects at (100) Si1âˆ’xGex/oxide interfaces. Microelectronic Engineering, 2011, 88, 383-387.	1.1	3

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73	Effects of surface passivation during atomic layer deposition of Al2O3 on In0.53Ga0.47As substrates. Microelectronic Engineering, 2011, 88, 431-434.	1.1	16
74	Design and analysis of the As implant-free quantum-well device structure. Microelectronic Engineering, 2011, 88, 358-361.	1.1	11
75	H2S molecular beam passivation of Ge(001). Microelectronic Engineering, 2011, 88, 399-402.	1.1	8
76	Silicon and selenium implantation and activation in In0.53Ga0.47As under low thermal budget conditions. Microelectronic Engineering, 2011, 88, 155-158.	1.1	20
77	Al2O3 stacks on In0.53Ga0.47As substrates: In situ investigation of the interface. Microelectronic Engineering, 2011, 88, 435-439.	1.1	4
78	Growth of high quality InP layers in STI trenches on miscut Si (001) substrates. Journal of Crystal Growth, 2011, 315, 32-36.	0.7	17
79	Numerical analysis of the new Implant-Free Quantum-Well CMOS: DualLogic approach. Solid-State Electronics, 2011, 63, 14-18.	0.8	4
80	Defect density reduction of the Al2O3/GaAs(001) interface by using H2S molecular beam passivation. Surface Science, 2011, 605, 1778-1783.	0.8	10
81	Ammonium sulfide vapor passivation of In0.53Ga0.47As and InP surfaces. Applied Physics Letters, 2011, 99, .	1.5	26
82	Atomic Layer Deposition of High-Îº Dielectrics on Sulphur-Passivated Germanium. Journal of the Electrochemical Society, 2011, 158, H687.	1.3	18
83	Towards Passivation of Ge(100) Surfaces by Sulfur Adsorption from a (NH4)2S Solution: A Combined NEXAFS, STM and LEED Study. Journal of the Electrochemical Society, 2011, 158, H589.	1.3	12
84	Self-Affine Surface Roughness of Chemically and Thermally Cleaned Ge(100) Surfaces. Journal of the Electrochemical Society, 2011, 158, H1090.	1.3	5
85	Heterogeneous Integration and Fabrication of III-V MOS Devices in a 200mm Processing Environment. ECS Transactions, 2011, 35, 299-309.	0.3	5
86	Electrical TCAD Simulations of a Germanium pMOSFET Technology. IEEE Transactions on Electron Devices, 2010, 57, 2539-2546.	1.6	92
87	Performance enhancement in Ge pMOSFETs with <100> orientation fabricated with a Si-compatible process flow. Microelectronic Engineering, 2010, 87, 2115-2118.	1.1	3
88	Si versus Ge for future microelectronics. Thin Solid Films, 2010, 518, 2301-2306.	0.8	19
89	P+/n junction leakage in thin selectively grown Ge-in-STI substrates. Thin Solid Films, 2010, 518, 2489-2492.	0.8	11
90	Fabrication of high quality Ge virtual substrates by selective epitaxial growth in shallow trench isolated Si (001) trenches. Thin Solid Films, 2010, 518, 2538-2541.	0.8	21

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91	Short-channel epitaxial germanium pMOS transistors. Thin Solid Films, 2010, 518, S88-S91.	0.8	5
92	Interface analysis of Ge ultra thin layers intercalated between GaAs substrates and oxide stacks. Thin Solid Films, 2010, 518, S123-S127.	0.8	6
93	Selective Epitaxial Growth of InP in STI Trenches on Off-Axis Si (001) Substrates. ECS Transactions, 2010, 27, 959-964.	0.3	13
94	Selective Area Growth of InP in Shallow-Trench-Isolated Structures on Off-Axis Si(001) Substrates. Journal of the Electrochemical Society, 2010, 157, H1023.	1.3	28
95	Effects of Halo Doping and Si Capping Layer Thickness on Total-Dose Effects in Ge p-MOSFETs. IEEE Transactions on Nuclear Science, 2010, 57, 1933-1939.	1.2	15
96	Calculation of the electron mobility in III-V inversion layers with high-Îº dielectrics. Journal of Applied Physics, 2010, 108, 103705.	1.1	29
97	High FET Performance for a Future CMOS $hbox{GeO}_{2}$ -Based Technology. IEEE Electron Device Letters, 2010, 31, 402-404.	2.2	50
98	(Invited) Exploring the ALD Al₂O₃/In_{0.53}Ga_{0.47}As and Al₂O₃/Ge Interface Properties: A Common Gate Stack Approach for Advanced III-V/Ge CMOS. ECS Transactions, 2010, 28, 173-183.	0.3	16
99	(Invited) Selective Epitaxial Growth of III-V Semiconductor Heterostructures on Si Substrates for Logic Applications. ECS Transactions, 2010, 33, 933-939.	0.3	9
100	Effective reduction of interfacial traps in Al2O3/GaAs (001) gate stacks using surface engineering and thermal annealing. Applied Physics Letters, 2010, 97, 112901.	1.5	66
101	On the interface state density at In0.53Ga0.47As/oxide interfaces. Applied Physics Letters, 2009, 95, .	1.5	99
102	A theoretical study of the initial oxidation of the GaAs(001)-Î²2(2Ã—4) surface. Applied Physics Letters, 2009, 95, .	1.5	31
103	The Fermi-level efficiency method and its applications on high interface trap density oxide-semiconductor interfaces. Applied Physics Letters, 2009, 94, .	1.5	50
104	Valence band energy in confined Si1â^'xGex (0.28<x<0.93) layers. Applied Physics Letters, 2009, 94, 172106.	1.5	18
105	Investigations of the Surface Chemical Composition and Atomic Structure of ex-situ Sulfur Passivated Ge(100). ECS Transactions, 2009, 25, 421-432.	0.3	4
106	The Influence of the Epitaxial Growth Process Parameters on Layer Characteristics and Device Performance in Si-passivated Ge pMOSFETs. ECS Transactions, 2009, 19, 183-194.	0.3	13
107	Thermal and Plasma Enhanced Atomic Layer Deposition of Al[sub 2]O[sub 3] on GaAs Substrates. Journal of the Electrochemical Society, 2009, 156, H255.	1.3	17
108	Ballistic current in metal-oxide-semiconductor field-effect transistors: The role of device topology. Journal of Applied Physics, 2009, 106, 053702.	1.1	2

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109	High-Hole-Mobility Silicon Germanium on Insulator Substrates with High Crystalline Quality Obtained by the Germanium Condensation Technique. Journal of the Electrochemical Society, 2009, 156, H208.	1.3	30
110	Implantation, Diffusion, Activation, and Recrystallization of Gallium Implanted in Preamorphized and Crystalline Germanium. Electrochemical and Solid-State Letters, 2009, 12, H417.	2.2	25
111	H[sub 2]O- and O[sub 3]-Based Atomic Layer Deposition of High-Îº Dielectric Films on GeO[sub 2] Passivation Layers. Journal of the Electrochemical Society, 2009, 156, G163.	1.3	31
112	Quantification of Drain Extension Leakage in a Scaled Bulk Germanium PMOS Technology. IEEE Transactions on Electron Devices, 2009, 56, 3115-3122.	1.6	29
113	Molecular beam epitaxy passivation studies of Ge and IIIâ€“V semiconductors for advanced CMOS. Microelectronic Engineering, 2009, 86, 1592-1595.	1.1	17
114	Adsorption of molecular oxygen on the reconstructed Î²2(2Ã—4)-GaAs(001) surface: A first-principles study. Surface Science, 2009, 603, 203-208.	0.8	33
115	Interfaces of high-k dielectrics on GaAs: Their common features and the relationship with Fermi level pinning (Invited Paper). Microelectronic Engineering, 2009, 86, 1529-1535.	1.1	49
116	A first-principles study of the structural and electronic properties of IIIâ€“V/thermal oxide interfaces. Microelectronic Engineering, 2009, 86, 1747-1750.	1.1	18
117	Electrical study of sulfur passivated In0.53Ga0.47As MOS capacitor and transistor with ALD Al2O3 as gate insulator. Microelectronic Engineering, 2009, 86, 1554-1557.	1.1	98
118	Electronic properties of Ge dangling bond centers at Si1â^'xGex/SiO2 interfaces. Applied Physics Letters, 2009, 95, 222106.	1.5	17
119	First-principles study of the electronic properties of Ge dangling bonds at (100)Si1â^'xGex/SiO2 interfaces. Applied Physics Letters, 2009, 95, .	1.5	10
120	Electrical Properties of III-V/Oxide Interfaces. ECS Transactions, 2009, 19, 375-386.	0.3	68
121	GaAs on Ge for CMOS. Thin Solid Films, 2008, 517, 148-151.	0.8	29
122	General 2D SchrÃ¶dinger-Poisson solver with open boundary conditions for nano-scale CMOS transistors. Journal of Computational Electronics, 2008, 7, 475-484.	1.3	3
123	On the characterisation of grown-in defects in Czochralski-grown Si and Ge. Journal of Materials Science: Materials in Electronics, 2008, 19, 24-31.	1.1	6
124	Device assessment of the electrical activity of threading dislocations in strained Ge epitaxial layers. Materials Science in Semiconductor Processing, 2008, 11, 364-367.	1.9	7
125	Electronic properties of (100)Ge/Ge(Hf)O2 interfaces: A first-principles study. Surface Science, 2008, 602, L25-L28.	0.8	38
126	High Ge content SGOI substrates obtained by the Ge condensation technique: A template for growth of strained epitaxial Ge. Thin Solid Films, 2008, 517, 23-26.	0.8	27

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127	Benefits and side effects of high temperature anneal used to reduce threading dislocation defects in epitaxial Ge layers on Si substrates. Thin Solid Films, 2008, 517, 172-177.	0.8	29
128	Influence of passivating interlayer on Ge/HfO2 and Ge/Al2O3 interface band diagrams. Materials Science in Semiconductor Processing, 2008, 11, 230-235.	1.9	7
129	Shallow boron implantations in Ge and the role of the pre-amorphization depth. Materials Science in Semiconductor Processing, 2008, 11, 368-371.	1.9	7
130	Accurate carrier profiling of n-type GaAs junctions. Materials Science in Semiconductor Processing, 2008, 11, 259-266.	1.9	4
131	On the Correct Extraction of Interface Trap Density of MOS Devices With High-Mobility Semiconductor Substrates. IEEE Transactions on Electron Devices, 2008, 55, 547-556.	1.6	339
132	Impact of Donor Concentration, Electric Field, and Temperature Effects on the Leakage Current in Germanium p $+/$n Junctions. IEEE Transactions on Electron Devices, 2008, 55, 2287-2296.	1.6	69
133	Ge dangling bonds at the (100)Ge/GeO2 interface and the viscoelastic properties of GeO2. Applied Physics Letters, 2008, 93, .	1.5	103
134	Applicability of Charge Pumping on Germanium MOSFETs. IEEE Electron Device Letters, 2008, 29, 1364-1366.	2.2	8
135	Characterization of Threading Dislocations in Thin Germanium Layers by Defect Etching: Toward Chromium and HF-Free Solution. Journal of the Electrochemical Society, 2008, 155, H677.	1.3	20
136	Processing Factors Impacting the Leakage Current and Flicker Noise of Germanium p[sup +]-n Junctions on Silicon Substrates. Journal of the Electrochemical Society, 2008, 155, H145.	1.3	9
137	First-principles study of the structural and electronic properties of (100)Geâˆ•Ge(M)O2 interfaces (M=Al,) Tj ETQq1 1 0.784314 rgBT /O	1.5	68
138	Capacitanceâ€“Voltage Characterization of GaAsâ€“Oxide Interfaces. Journal of the Electrochemical Society, 2008, 155, H945.	1.3	55
139	Atomic Layer Deposition of Hafnium Oxide on Ge and GaAs Substrates: Precursors and Surface Preparation. Journal of the Electrochemical Society, 2008, 155, H937.	1.3	35
140	Capacitance-voltage characterization of GaAsâ€“Al2O3 interfaces. Applied Physics Letters, 2008, 93, 183504.	1.5	109
141	Structure and interface bonding of GeO2âˆ•Geâˆ•In0.15Ga0.85As heterostructures. Applied Physics Letters, 2008, 93, 133504.	1.5	9
142	Germanium MOSFET Devices: Advances in Materials Understanding, Process Development, and Electrical Performance. Journal of the Electrochemical Society, 2008, 155, H552.	1.3	230
143	Low temperature mobility in hafnium-oxide gated germanium p-channel metal-oxide-semiconductor field-effect transistors. Applied Physics Letters, 2007, 91, 263512.	1.5	6
144	Surface recombination velocity in GaAs and In0.15Ga0.85As thin films. Applied Physics Letters, 2007, 90, 134102.	1.5	16

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145	Electrical Passivation of the (100)Ge Surface by Its Thermal Oxide. ECS Transactions, 2007, 11, 451-459.	0.3	6
146	First-Principles Investigation of (100)Ge/Ge(Hf)O2 Interfaces. ECS Transactions, 2007, 11, 471-478.	0.3	4
147	Origin and Suppression of Junction Leakage in Germanium-On-Silicon Structures. ECS Transactions, 2007, 6, 31-39.	0.3	0
148	High Mobility Strained Ge pMOSFETs With High-$kappa$ /Metal Gate. IEEE Electron Device Letters, 2007, 28, 825-827.	2.2	40
149	H2S exposure of a (100)Ge surface: Evidences for a (2Ã—1) electrically passivated surface. Applied Physics Letters, 2007, 90, 222105.	1.5	32
150	Germanium: The Past and Possibly a Future Material for Microelectronics. ECS Transactions, 2007, 11, 479-493.	0.3	33
151	Characteristic trapping lifetime and capacitance-voltage measurements of GaAs metal-oxide-semiconductor structures. Applied Physics Letters, 2007, 91, 133510.	1.5	94
152	Germanium FETs and capacitors with rare earth CeO2/HfO2 gates. Solid-State Electronics, 2007, 51, 1508-1514.	0.8	21
153	Electrical and reliability characterization of metal-gate/HfO2/Ge FETâ€™s with Si passivation. Microelectronic Engineering, 2007, 84, 2067-2070.	1.1	35
154	Comparing GaAs and In0.15Ga0.85As as channel material for alternative substrate CMOS. Microelectronic Engineering, 2007, 84, 2154-2157.	1.1	5
155	Experimental and theoretical study of Ge surface passivation. Microelectronic Engineering, 2007, 84, 2267-2273.	1.1	19
156	Germanium MOSFETs With $hbox{CeO}_{2}/hbox{HfO}_{2}/ hbox{TiN}$ Gate Stacks. IEEE Transactions on Electron Devices, 2007, 54, 1425-1430.	1.6	37
157	High-Performance Deep Submicron Ge pMOSFETs With Halo Implants. IEEE Transactions on Electron Devices, 2007, 54, 2503-2511.	1.6	88
158	Lifetime and leakage current considerations in metal-doped germanium. Journal of Materials Science: Materials in Electronics, 2007, 18, 799-804.	1.1	16
159	Determining weak Fermi-level pinning in MOS devices by conductance and capacitance analysis and application to GaAs MOS devices. Solid-State Electronics, 2007, 51, 1101-1108.	0.8	18
160	Study of the Junction Depth Effect on Ballistic Current Using the Subband Decomposition Method. , 2007, , 205-208.		1
161	New interface state density extraction method applicable to peaked and high-density distributions for Ge MOSFET development. IEEE Electron Device Letters, 2006, 27, 405-408.	2.2	69
162	HfO2 as gate dielectric on Ge: Interfaces and deposition techniques. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 135, 256-260.	1.7	68

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